SMALL SIGNAL SCHOTTKY DIODES

VOLTAGE RANGE: 20 V
POWER DISSIPATION: 430 mW

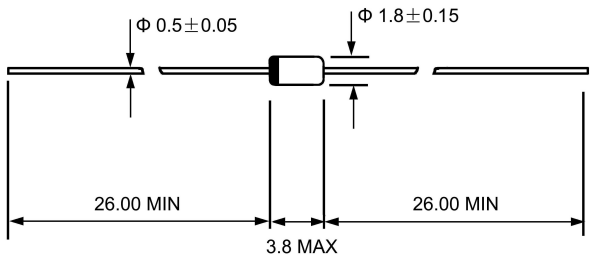
FEATURES

- ◇ Metal-to-silicon junction
- ◇ High breakdown voltage
- ◇ Low turn-on voltage
- ◇ Ultrafast switching speed
- ◇ Prmarly intended for high level UHF/VHF detection and pulse applications with broad dynamic range

MECHANICAL DATA

- ◇ Case:JEDEC DO--35,glass case
- ◇ Polarity: Color band denotes cathode end
- ◇ Weight: Approx. 0.13 gram

DO - 35(GLASS)



Dimensions in millimeters

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	UNITS
Peak reverse voltage	V_{RRM}	20.0	V
Power dissipation (Infinite Heat Sink)	P_{tot}	430.0	mW
Forward continuous current	I_{FSM}	35.0	mA
Junction and storage temperature range	T_J/T_{STG}	-55 ---+ 150	℃
Maximum lead temperature for soldering during 10S at 4mm from case	T_L	230	℃

ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	UNITS
Reverse breakdown voltage @ I_R=10μA	V_R	20.0			V
Leakage current @ V_R=16V	I_R			150	nA
Forward voltage drop @ I_F=1mA Test pulse: tp≤300μs δ<2% I_F=35mA	V_F			0.41 1.0	V
Junction capacitance @ V_R=0V,f=1MHz	C_J			2	pF
Thermal resistance	$R_{\theta JA}$			400	K/W

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FIG.1 – TYPICAL CURRENT VERSUS FORWARD VOLTAGE AT DIFFERENT TEMPERATURES (TYPICAL VALUES)

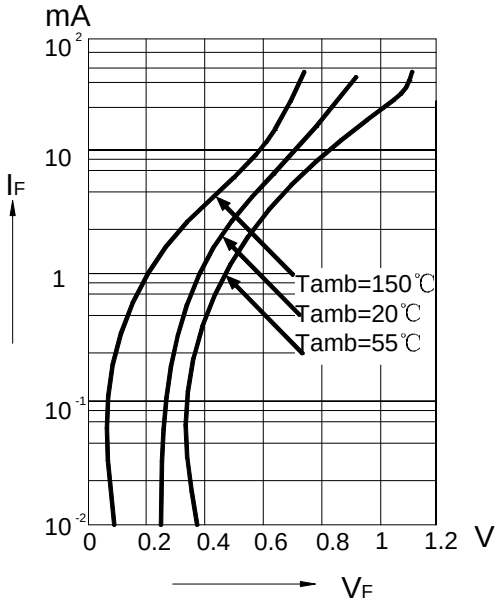

FIG.2 –FORWARD CURRENT VERSUS FORWARD VOLTAGE (TYPICAL VALUES)

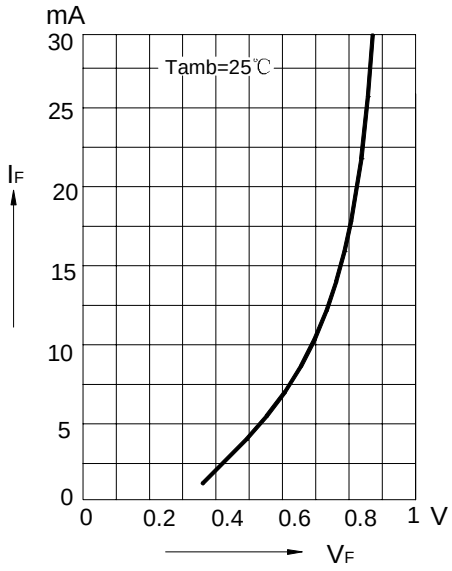

FIG.3 –REVERSE CURRENT VERSUS AMBIENT TEMPERATURE

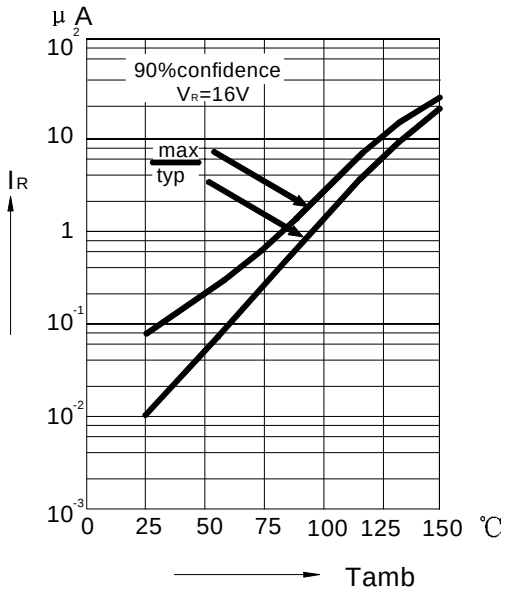

FIG.4 – REVERSE CURRENT VERSUS CONTINUOUS REVERSE VOLTAGE (TYPICAL VALUES)

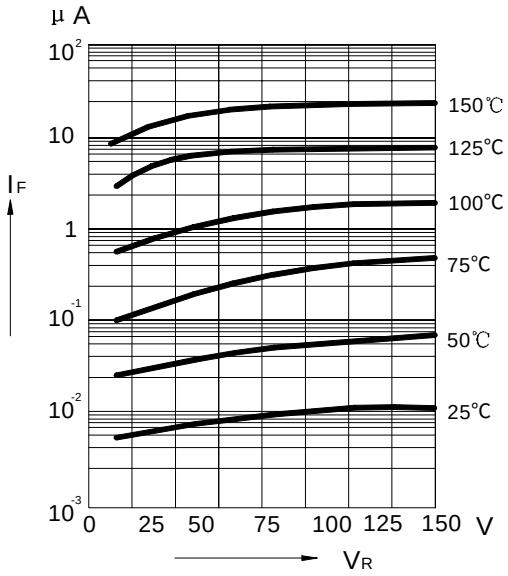

FIG.5 – CAPACITANCE CVERSUS REVERS APPLIED VOLTAGE VR (TYPICAL VALUES)